



Form 1449 (Modified)	Atty Docket No. UNTYP023	Application No.: 10/605,963
Information Disclosure Statement By Applicant	Applicant: Rinerson, et al.	
(Use Several Sheets if Necessary)	Filing Date November 10, 2003	Group 2818

U.S. Patent Documents (Copies not supplied by Applicant)

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub- class	Filing Date
TL	A	6,204,139	03/20/01	Liu, et al.	438	385	8/25/1998
J	B	6,249,014	06/19/01	Bailey	257	295	10/1/1998
V	C	6,456,525	09/24/02	Perner, et al.	365	171	9/15/2000

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
TL	D	Beck, A. et al., "Reproducible switching effect in thin oxide films for memory applications," Applied Physics Letters, Vol. 77, No. 1, 3 July 2000, 139-141.
TL	E	Liu, S.Q., et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films", Applied Physics Letters, Vol. 76, No. 19, 8 May 2000, 2749-2651.
TL	F	Liu, S.Q., et al., "A New Concept For Non-Volatile Memory: Electric-Pulse Induced Reversible Resistance Change Effect In Magnetoresistive Films", Space Vacuum Epitaxy Center, University of Huston, Huston TX, 7 Pages.
TL	G	Park, In Seon et al., "Ultra-thin EBL (encapsulated barrier layer) for Ferroelectric Capacitor," IDEM, Vol 97, 617- 620.
TL	H	Rossel, C. et al., "Electrical current distribution across a metal-insulator-metal structure during bistable switching," Journal of Applied Physics, Vol. 90, No. 6, 15 September 2001, 2892-2898.
TL	I	Watanabe, Y. et al., "Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped SrTiO ₃ single crystals," Applied Physics Letters, Vol. 78, No. 23, 4 June 2001, 3738-3740.
TL	J	Yoon, Dong-Soon et al., "High Performance of Novel Oxygen Diffusion Barrier Materials for Future High-Density Dynamic Random Access Memory Devices," IEEE Transactions on Electron Devices, Vol 49, No 11, November 2002, 1917-1927.
Examiner	Date Considered	
Maole	12/15/04	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.